

Acknowledgement

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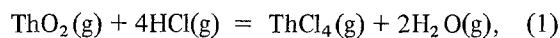
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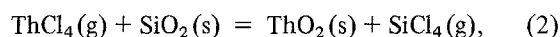
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Preparation of ThSiO₄ single crystals by a vapour phase reaction

Thorium silicate is the only ternary compound which exists in the ThO₂ and SiO₂ system [1, 2]. Thorium silicate single crystals were synthesized by the reaction of an aqueous solution of thorium chloride with pyrex glass [3]. The present paper reports a similar process for the preparation of ThSiO₄ crystals using a vapour phase reaction. In the study of chemical transport reactions of uranium and thorium oxides the author has prepared single crystals of ThSiO₄ using halogen gases [4]. When ThO₂ source material is sealed in a quartz tube with HCl or Cl₂ gas as a transport agent and placed in the hot zone, ThSiO₄ single crystals can be produced almost in the cold zone in the quartz tube. The crystal is about 1 × 0.7 × 0.5 mm³ in size and is transparent with many faces. The possible reactions are considered as follows:



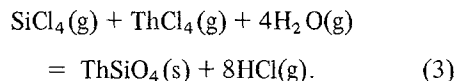
some parts of ThCl₄(g) would react with the quartz tube,



and then the formation of ThSiO₄ crystals proceeds in the colder zone as,

TABLE I Preparation conditions of ThSiO₄ crystals

	ThO ₂ + HCl	ThO ₂ + Cl ₂
Source temperature (° C)	1050	1050
Deposition temperature (° C)	950	950
Pressure of halogen (atm at 1000° C)	3.49	1.56
Transport time (h)	347	936
Transport rate (mg h ⁻¹)	0.17	0.26
Crystal size (mm ³)	0.2 × 0.2 × 0.2	1 × 0.7 × 0.5



Evidence that ThSiO₄ crystals may be prepared using a vapour phase reaction (Equation 3) is due to the facts:

(1) ThSiO₄ crystals can be produced in the cold zone more readily than in intermediate or hot zones.

(2) The crystals produced are randomly distributed in the cold zone as is usual in the case of chemical transport reactions, and not uniformly deposited all over the tube, as is the coating produced by the direct reaction of ThCl₄(g) with the quartz tube.

When the temperature at the cold zone is below

900°C, the crystals of ThSiO₄ are scarcely produced.

Table I shows the preparation conditions. When uranium dioxide co-exists with ThO₂ in the hot zone, the crystals of ThSiO₄ produced become green and transparent. Even in these cases the lattice constants of ThSiO₄ do not vary, so that the solubility of uranium in ThSiO₄ is deduced to be so small as to be only a degree of order of doping. Fig. 1 shows a crystal of ThSiO₄ doped with uranium which is green in colour. The lattice parameters of the ThSiO₄ produced were $a_0 = 7.090 \pm 0.004 \text{ \AA}$ and $c_0 = 6.317 \pm 0.004 \text{ \AA}$

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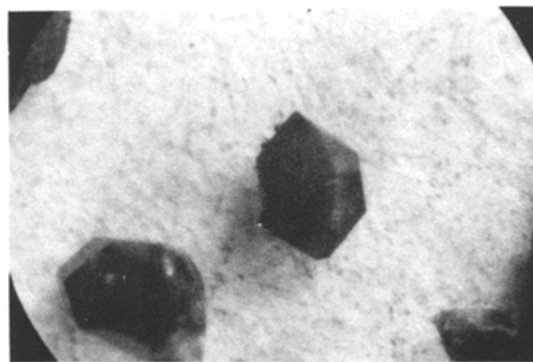


Figure 1 ThSiO₄ crystals doped with uranium (green in colour). Maximum length is about 1 mm.

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The morphology of single crystals during compressive creep testing

Several investigators [1–3] reported that the change in morphology of single crystals undergoing compressive creep is a function of the loading system and that the shape of the creep curve is related to the morphology. Although their analyses were based on observations made on specimens at the completion of the creep test, the observations suggested that the type of morphology was directly related to the various stages of creep, i.e. primary, steady-state, etc. The present study was conducted to record the morphology changes of a specimen during a compressive creep test.

Time lapse photography was used to observe and record pictorially the specimen morphology as it deformed. After placing the specimen in the furnace, the telescope and camera were aligned so that the specimen could be clearly seen through

the viewfinder of the camera. Focusing was done at room temperature by adjusting the objective lens of the telescope and the camera's focusing ring. At the temperatures (1000°C to 1300°C) employed during these experiments, the interior of the furnace essentially became a black body, making it impossible to distinguish the specimen from the background of the furnace. A blue glass filter was used to eliminate most of the light radiated by the hot furnace. To provide the contrast required for photography, a high intensity white light source of at least 300 W was used to illuminate the specimen. The blue filter, although filtering out most of the light created by the high temperature conditions, would allow enough light to pass through to enable the image of the specimen to be recorded. A Kodak Cine-Special 16 mm movie camera with double X negative film was used to record the specimen morphology. Generally, 12 frames per minute were exposed during the experiment.